

ABSTRACT

INSULATING STRUCTURE AND PRODUCTION METHOD OF SAME TECHNICAL
FIELD

5 An insulating structure is formed that favorably
maintains gap-fill capability of a narrow width pattern
in a memory cell while also preventing the formation of
cracks in an insulator in a peripheral circuit, and has
the memory cell and peripheral circuit within the same
layer. The present invention provides an insulating
structure comprising a substrate and a circuit pattern
10 formed on the substrate, wherein the circuit pattern has
a narrow width region having a narrow width pattern of a
width of 30 nm or less and a wide width region having a
wide width pattern of a width of greater than 100 nm in
the same layer, and the same insulating composition is
15 formed within the narrow width pattern and within the
wide width pattern.

Figure 1